

**HANDSET RF MODULE**

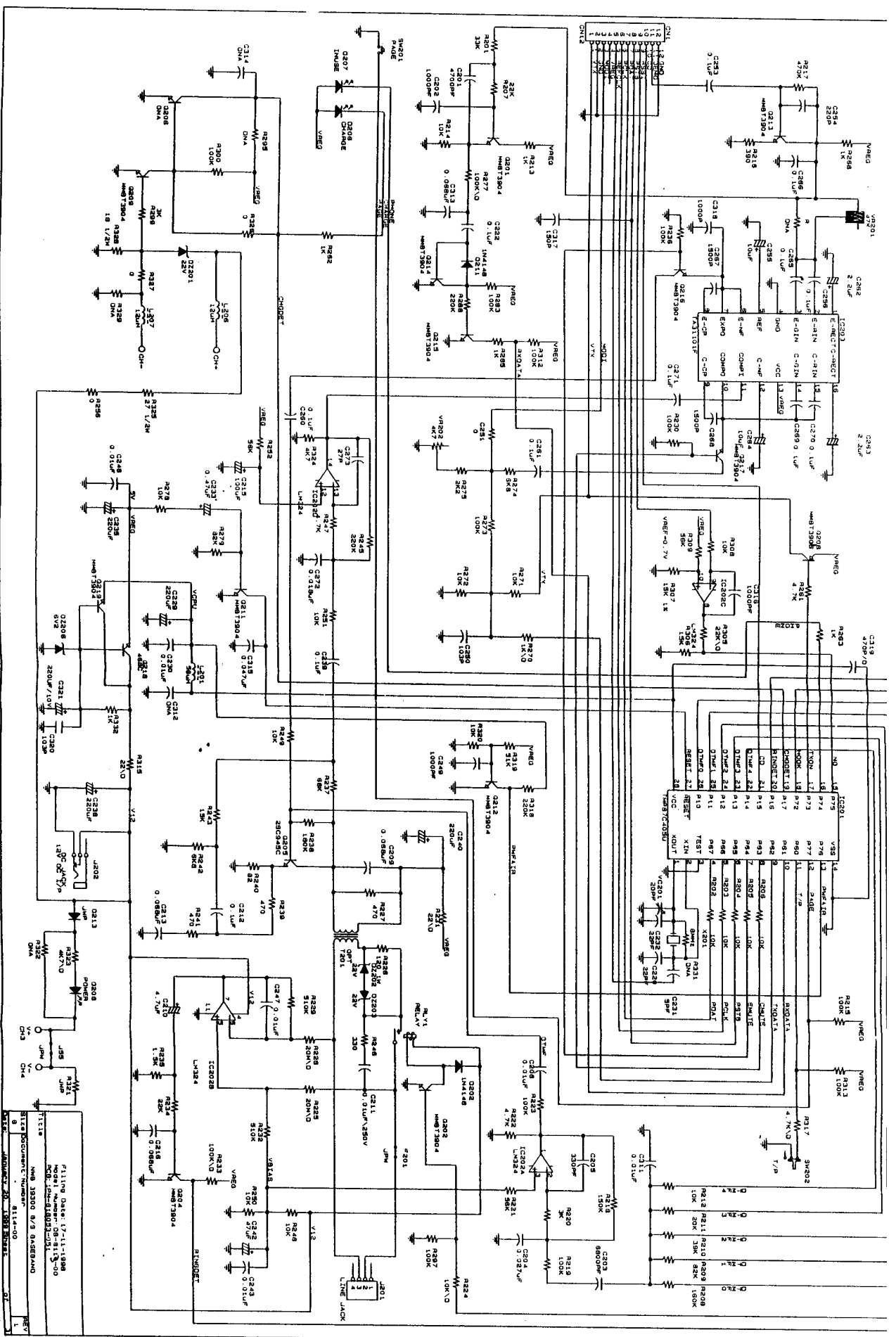
- P1: VTX
- P2: GND
- P3: TX-AF
- P4: VCC
- P5: RECCLK
- P6: RCLK
- P7: BDATA
- P8: BSTR
- P9: V-RSSI
- P10: CR-DET
- P11: RX-AF
- P12: GND

**DUPLEX**

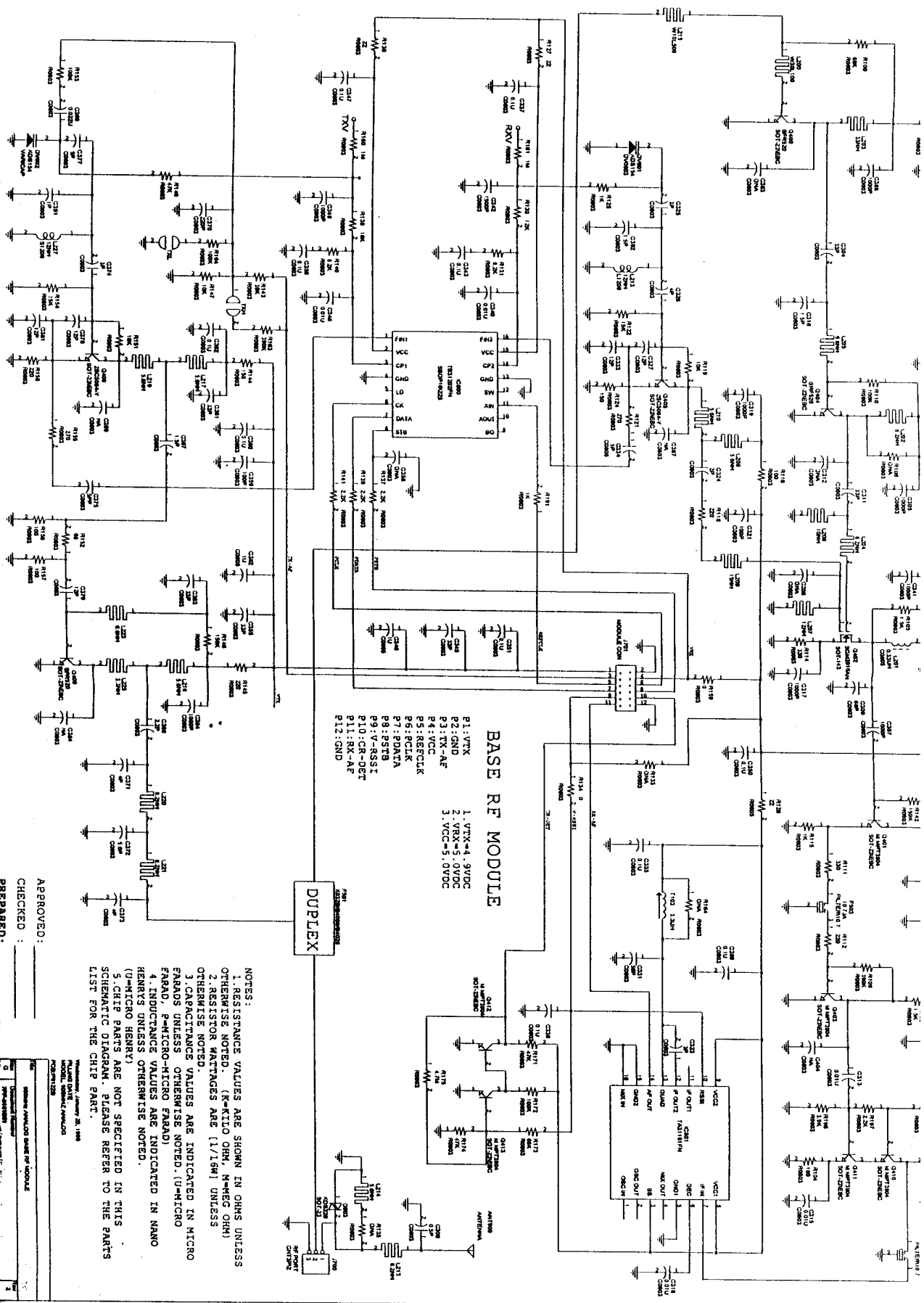
**NOTES:**  
 1. RESISTANCE VALUES ARE SHOWN IN OHMS UNLESS OTHERWISE NOTED. (R-KILO OHM, M-MEG OHM)  
 2. RESISTOR WATTAGES ARE [1/16W] UNLESS OTHERWISE NOTED.  
 3. CAPACITANCE VALUES ARE INDICATED IN MICRO FARADS UNLESS OTHERWISE NOTED. (U-MICRO FARAD, P-MICRO-MICRO FARAD)  
 4. INDUCTANCE VALUES ARE INDICATED IN NANO HENRYS UNLESS OTHERWISE NOTED.  
 5. CHIP PARTS ARE NOT SPECIFIED IN THIS SCHEMATIC DIAGRAM. PLEASE REFER TO THE PARTS LIST FOR THE CHIP PART.

APPROVED: \_\_\_\_\_  
 CHECKED: \_\_\_\_\_  
 PREPARED: \_\_\_\_\_

NO.	REVISION	DESCRIPTION	DATE
1		ISSUED FOR PRODUCTION	10/10/88
2		REVISED	11/10/88



Filing Date: 17-11-1988  
 Model Number: 08-8115-00  
 Part Number: 08-8115-00  
 NAB 3500 B/A BASEBAND  
 Sizer Document Number: 8114-00  
 1



**BASE RF MODULE**

- P1: VTX
- P2: GND
- P3: TX-AF
- P4: VCC
- P5: RECCLK
- P6: RCLK
- P7: PDATA
- P8: PSYB
- P9: V-RSSI
- P10: CR-DET
- P11: RX-AF
- P12: GND

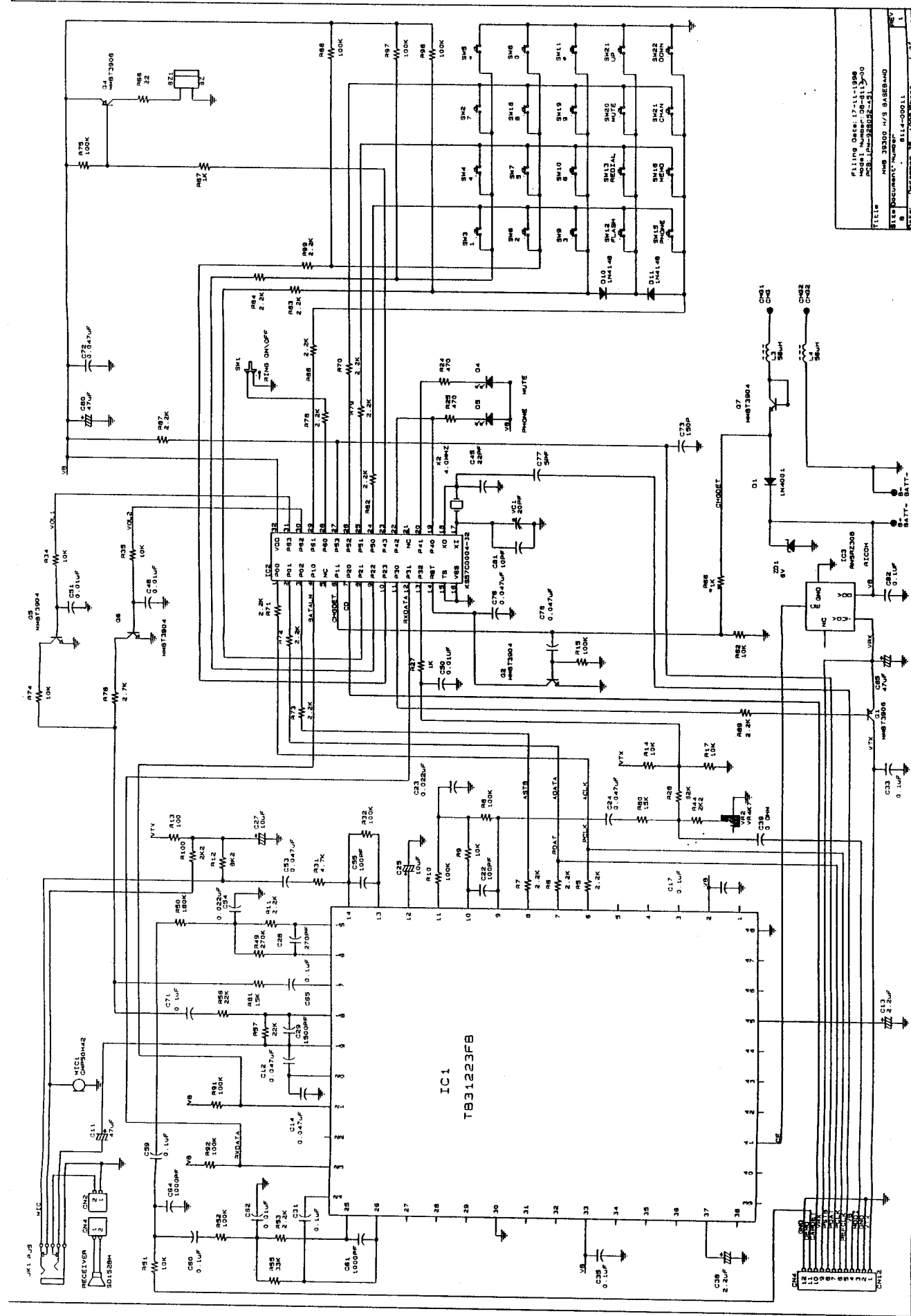
**DUPLEX**

**NOTES:**

1. RESISTANCE VALUES ARE SHOWN IN OHMS UNLESS OTHERWISE NOTED. (K=KILO OHM, M=MEG OHM)
2. RESISTOR WATTAGES ARE (1/16W) UNLESS OTHERWISE NOTED.
3. CAPACITANCE VALUES ARE INDICATED IN MICRO FARADS UNLESS OTHERWISE NOTED. (U=MICRO FARAD, P=MICRO-MICRO FARAD)
4. INDUCTANCE VALUES ARE INDICATED IN NANO HENRYS UNLESS OTHERWISE NOTED.
5. CHIP PARTS ARE NOT SPECIFIED IN THIS SCHEMATIC DIAGRAM. PLEASE REFER TO THE PARTS LIST FOR THE CHIP PART.

APPROVED: \_\_\_\_\_  
 CHECKED: \_\_\_\_\_  
 PREPARED: \_\_\_\_\_

DATE	REVISION	BY	REASON
1988-08-23	1	MM	INITIAL DESIGN
1988-08-23	2	MM	REVISION
1988-08-23	3	MM	REVISION
1988-08-23	4	MM	REVISION
1988-08-23	5	MM	REVISION



Filing Date: 17-11-1998  
 Model Number: DB-511-300  
 Title: DB-511-300-551  
 Drawing Number: 11-11-0011  
 Date: 11-11-98